

NE3521M04

Data Sheet
 R09DS0058EJ0100
 Rev.1.00
 Mar 19, 2013

N-Channel GaAs HJ-FET, K Band Low Noise and High-Gain

FEATURES

- Low noise figure and high associated gain:
 $NF = 0.85 \text{ dB TYP.}, Ga = 11 \text{ dB TYP. @ } V_{DS} = 2 \text{ V}, I_D = 10 \text{ mA}, f = 20 \text{ GHz}$
 $NF = 0.9 \text{ dB TYP.}, Ga = 10.5 \text{ dB TYP. @ } V_{DS} = 2 \text{ V}, I_D = 6 \text{ mA}, f = 20 \text{ GHz}$ (Reference Value)
- Flat-lead 4-pin thin-type super minimold (M04) package

APPLICATIONS

- DBS LNB gain-stage, Mix-stage
- Low noise amplifier for microwave communication system

ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Marking	Supplying Form
NE3521M04-T2	NE3521M04-T2-A	Flat-lead 4-pin thin-type super minimold (M04) (Pb-Free)	3 kpcs/reel	V86	<ul style="list-style-type: none"> • Embossed tape 8 mm wide • Pin 1 (Source), Pin 2 (Drain) face the perforation side of the tape
NE3521M04-T2B	NE3521M04-T2B-A		15 kpcs/reel		

Remark To order evaluation samples, contact your nearby sales office.
 Part number for sample order: NE3521M04-A

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	V_{DS}	4.0	V
Gate to Source Voltage	V_{GS}	-3.0	V
Drain Current	I_D	I_{DSS}	mA
Gate Current	I_G	80	μA
Total Power Dissipation ^{Note}	P_{tot}	125	mW
Channel Temperature	T_{ch}	+125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +125	$^\circ\text{C}$

Note: Mounted on $1.08 \text{ cm}^2 \times 1.0 \text{ mm}$ (t) glass epoxy PWB

CAUTION

Observe precautions when handling because these devices are sensitive to electrostatic discharge.

RECOMMENDED OPERATING RANGE ($T_A = +25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V_{DS}	1	2	3	V
Drain Current	I_D	3	10	15	mA
Input Power	P_{in}	–	–	0	dBm

ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

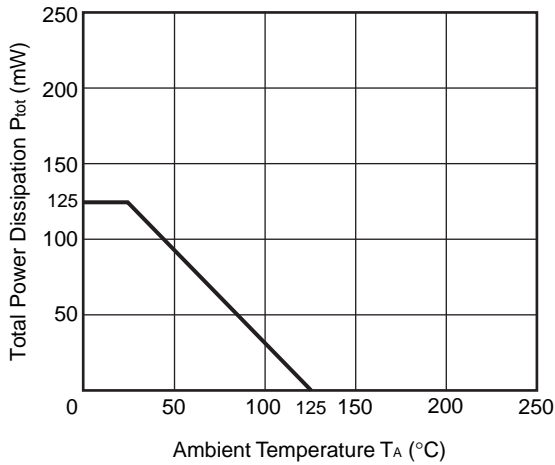
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	I_{GSO}	$V_{GS} = -3.0\text{ V}$	–	0.5	10	μA
Saturated Drain Current	I_{DSS}	$V_{DS} = 2\text{ V}, V_{GS} = 0\text{ V}$	25	45	70	mA
Gate to Source Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 2\text{ V}, I_D = 100\ \mu\text{A}$	-0.2	-0.7	-1.3	V
Transconductance	gm	$V_{DS} = 2\text{ V}, I_D = 10\text{ mA}$	50	–	–	mS
Noise Figure	NF	$V_{DS} = 2\text{ V}, I_D = 10\text{ mA}, f = 20\text{ GHz}$	–	0.85	1.2	dB
Associated Gain	Ga		9	11	–	dB

**STANDARD CHARACTERISTICS FOR REFERENCE
($T_A = +25^\circ\text{C}$, unless otherwise specified)**

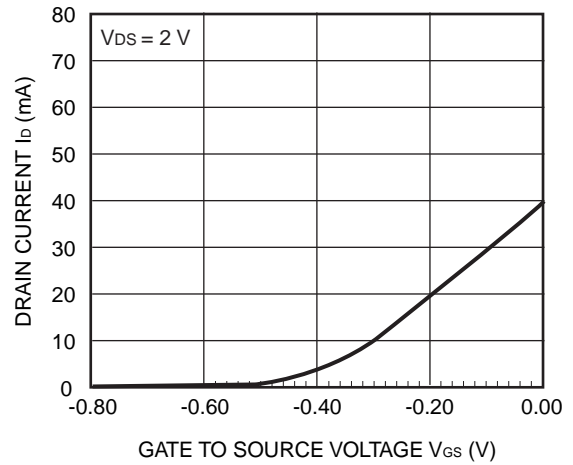
Parameter	Symbol	Test Conditions	Reference Value	Unit
Noise Figure	NF	$V_{DS} = 2\text{ V}, I_D = 6\text{ mA}, f = 20\text{ GHz}$	0.9	dB
Associated Gain	Ga		10.5	dB

TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

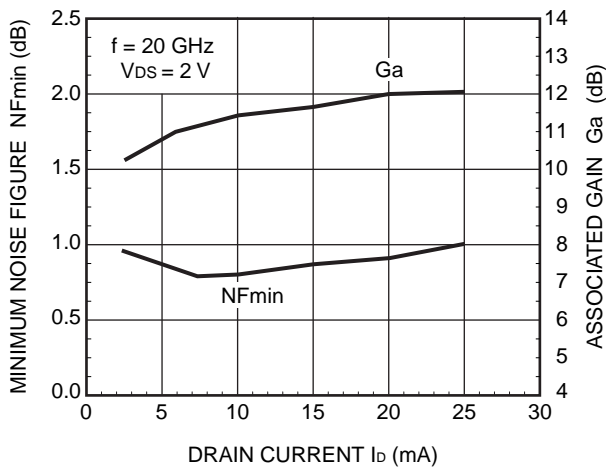
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



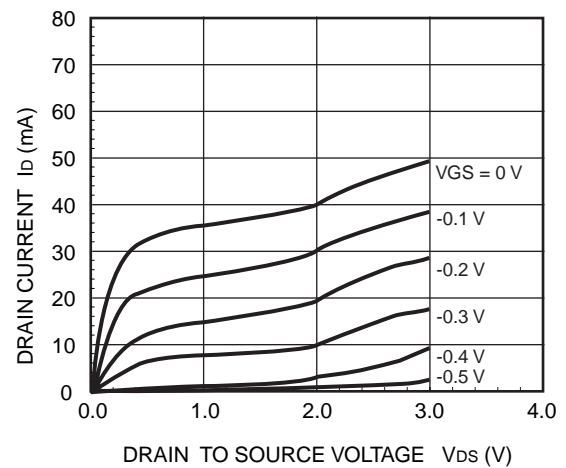
DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE



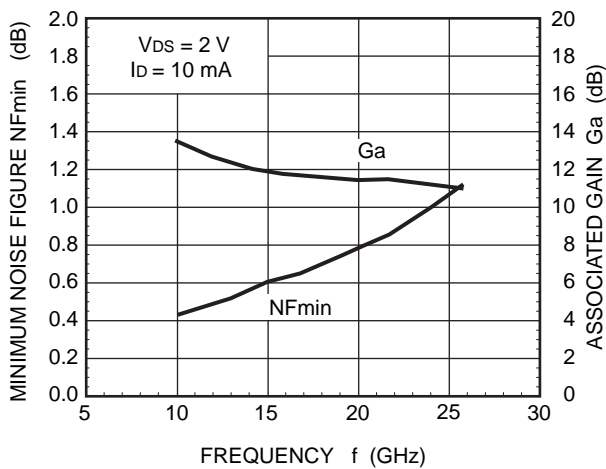
MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. DRAIN CURRENT



DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. FREQUENCY



Remark The graphs indicate nominal characteristics.

S-PARAMETERS

S-parameters and noise parameters are provided on our web site in a form (S2P) that enables direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.

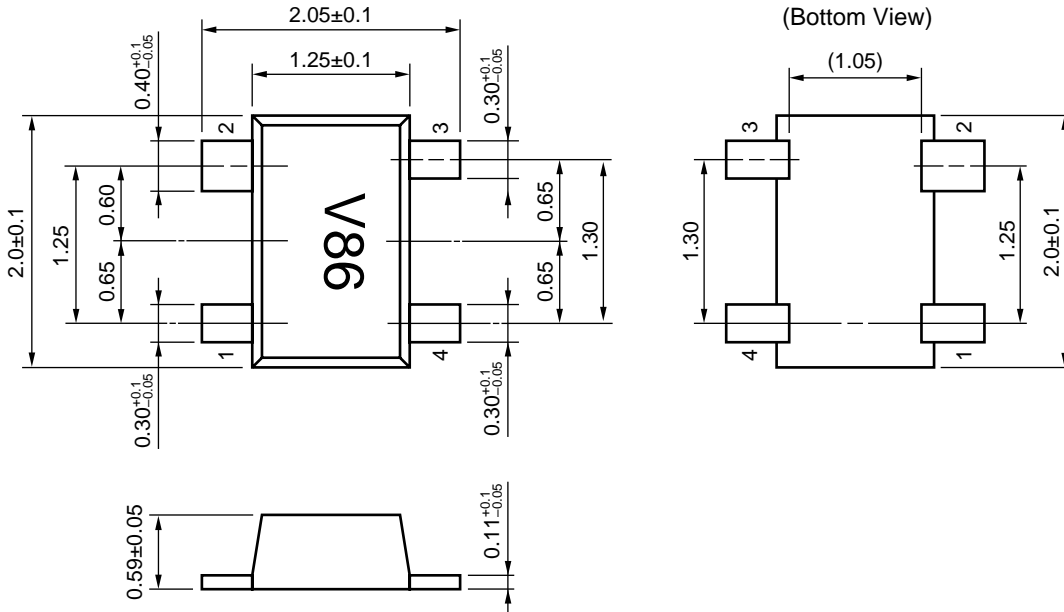
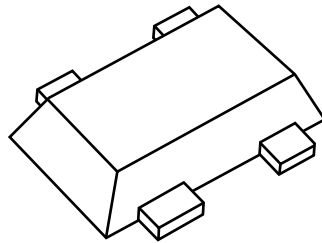
Click here to download S-parameters.

[Products] → [RF Devices] → [Device Parameters]

URL <http://www.renesas.com/products/microwave/>

PACKAGE DIMENSIONS

FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04) (UNIT: mm)



PIN CONNECTIONS

- 1. Source
- 2. Drain
- 3. Source
- 4. Gate

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2% (Wt.) or below	IR260
Partial Heating	Peak temperature (package surface temperature) : 350°C or below Soldering time (per side of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2% (Wt.) or below	HS350

CAUTION

Do not use different soldering methods together (except for partial heating).

Caution	GaAs Products	<p>This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.</p> <ul style="list-style-type: none">• Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.<ol style="list-style-type: none">1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.• Do not burn, destroy, cut, crush, or chemically dissolve the product.• Do not lick the product or in any way allow it to enter the mouth.
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Revision History	NE3521M04 Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Mar 19, 2013	-	First edition issued

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